UvA-VU Master Course: Advanced Solid State Physics

Contents in 2005:

- Diffraction from periodic structures (week 6, AdV)
- Electronic band structure of solids (week 7, AdV)
- **Motion of electrons and transport phenomena** (week 8, AdV)
- Superconductivity (week 9&10, RW)
- Magnetism (week 11&12,JB)

Literature, software and homework

The course is based on the book:

H. Ibach and H. Lüth: Solid State Physics 3r^d edition (Springer-Verlag, Berlin, 2003) ISBN 3-540-43870-X

See also:

N.W. Ashcroft and N.D. Mermin: Solid State Physics (Saunders College Publ.) ISBN 0-03-083993-9

Computer simulations form an essential part of the course:

R.H. Silsbee and J. Dräger: Simulations for Solid State Physics (Cambridge University Press, Cambridge 1997) ISBN 0-521-59911-3Software (freeware): www.physics.cornell.edu/sss/

Homework exercises will be distributed throughout the course Completing the course gives 6 ECTS \rightarrow ~ 6 x 28 hours

Course 3: Motions of electrons and transport phenomena

Pictures are taken from the Solid State Course by Mark Jarrel (Cincinnati University), from Ibach and Lüth, from Ashcroft and Mermin and from several sources on the web.

Course 3: Motions of electrons and transport phenomena

- Equation of motion of electrons
- Drude and Sommerfeld models for conductivity
- Crystal momentum is not momentum!
- Motion of electrons in bands and the effective mass tensor
- Currents in bands and holes
- Scattering of electrons in bands
- Electrical conductivity of metals
- Quantum oscillations and the topology of Fermi surfaces
- Quantum Hall effect

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Equation of motion of electrons

Classical equation of motion in **E** and **B** field:

$$
\vec{F} = m \frac{d\vec{v}}{dt} = -e(\vec{E} + \vec{v} \times \vec{B})
$$
without collisions
\n
$$
\vec{F} = m \left(\frac{d\vec{v}}{dt} + \frac{\vec{v}}{\tau}\right) = -e(\vec{E} + \vec{v} \times \vec{B})
$$
with collisions
\n
$$
\vec{F} = m \left(\frac{d\vec{v}}{dt} + \frac{\vec{v}}{\tau}\right) = -e(\vec{E} + \vec{v} \times \vec{B})
$$
with collisions
\n
$$
\vec{F} = \vec{v}_{av} = -\frac{e\vec{E}\tau}{m}
$$

\n
$$
\vec{v} = \vec{v}_{av} = -\frac{e\vec{E}\tau}{m}
$$

\ncurrent density
\n
$$
\vec{j} = -ne\vec{v}_{av} = -ne\left(-\frac{e\vec{E}\tau}{m}\right)
$$

Drude model for conductivity

E m

 \rightarrow

ne

 ρ = resistivity

 σ = conductivity

 $\|$ $\overline{}$

⎠

⎞

 \bullet collisions probability 1/ τ (time between collisions τ)

 $\overline{\overline{c}}$ \overline{c} \overline{c} \overline{c} \overline{c} \overline{c} \overline{c} \overline{c} \overline{c} \overline{c} \overline{c}

 $\overline{}$ $\overline{}$

⎝

 $\bigg($

 $j = \sigma E = \rho^{-1}E$ $\vec{j}=\sigma\ \vec{E}=\rho^{-1}\vec{E}$

 $\vec{j} = -ne\vec{v}_{av} = -ne\left(-\frac{eE}{\sigma}\right)$

 $=-nev_{\infty} = -ne^{-1}$

• thermal equilibrium through collisions

m

 \rightarrow

Paul Drude(1863-1906)

- Maxwell-Boltzmannvelocity distribution equipartition of energy 1/2 mv_T² = 3/2 k_BT

$$
\sigma = \frac{ne^2\tau}{m}
$$

electron transport with v_{av}=v_D = drift velocity

τ ~ 10⁻¹⁴ - 10⁻¹⁵ s, v_T ~ 10⁵ m/s mean free path $\ell=$ v $_\mathsf{T}$ τ = 1-10 Å

Important failure Drude: mean free path ℓ can be $\bm{>}$ interatomic distance

Sommerfeld model for conductivity

Intermezzo: Crystal momentum is not momentum!

• Free electron with energy $\bm{\mathrm{\epsilon}}_{\mathsf{k}}$ in state $\bm{\mathrm{\psi}}_{\mathsf{k}}$

$$
H\psi_k = \varepsilon_k \psi_k \hspace*{0.2cm} ; \hspace*{0.2cm} H = -\frac{\hbar^2}{2m} \frac{d^2}{dx^2} \hspace*{1cm} \psi_k = \frac{1}{\sqrt{L}} e^{ikx} \hspace*{0.2cm} ; \hspace*{0.2cm} \varepsilon_k = \frac{\hbar^2 k^2}{2m}
$$

Momentum expectation value free electrons

$$
p_k = \langle \psi_k | - i\hbar \frac{d}{dx} | \psi_k \rangle = \int \frac{1}{\sqrt{L}} e^{-ikx} \left(-i\hbar \frac{d}{dx} \right) \frac{1}{\sqrt{L}} e^{ikx} dx = \hbar k
$$

• Bloch electrons

$$
H = -\frac{\hbar^2}{2m} \frac{d^2}{dx^2} + V(x) \qquad p_k = \int u_k^*(x)e^{-ikx}u_k^*(x) \left(-i\hbar \frac{d}{dx}\right)u_k(x)e^{ikx}dx
$$

$$
\psi_k(x) = u_k(x)e^{ikx} \qquad = \hbar k - i\hbar \int u_k^*(x)\frac{du_k}{dx}dx \neq \hbar k
$$

Motion of electrons in bands and effective mass tensor

• the real world: electron state is wave packet delocalized

$$
\psi(x,t) = \frac{1}{2\pi} \int_{-\infty}^{\infty} U(k)e^{i(kx-\omega(k)t)}d\vec{k}
$$

$$
U(k) = const. \delta(k - k_0) \rightarrow \psi(x, t) \propto e^{i(k_0 x - \omega t)}
$$

 $i (\frac{1}{k} x \cdot \omega t)$

$$
U(k) = const. \rightarrow \psi(x, t) \propto \delta(x)
$$
 localized

• group velocity and dispersion

$$
v = \frac{\partial \omega}{\partial k} \quad ; \quad \omega = c(k)k
$$

• velocity of crystal electron depends on dispersion E(**k**)

$$
\vec{v} = \vec{\nabla}_k \omega(\vec{k}) = \frac{1}{\hbar} \vec{\nabla}_k E(\vec{k})
$$

free electrons: $E = \hbar^2 k^2 / 2m$ **^v**= **k**h/m = **p**/m

Velocity of crystal electron

Example: tight binding dispersion relation

$$
\varepsilon_k = E_{at} + A + 2B\cos(ka)
$$

velocity

$$
\vec{v}_k = \frac{1}{\hbar} \vec{\nabla}_k E(\vec{k})
$$

$$
v_k = -2Ba\sin(ka)
$$

velocity is constant at fixed k very different from classical picture

Semi classical eq. of motion in electric field

• rate of change of group velocity component

$$
\dot{v}_i = \frac{1}{\hbar} \frac{d}{dt} \left(\vec{\nabla}_k E \right)_i = \frac{1}{\hbar} \sum_j \frac{\partial^2 E}{\partial k_i \partial k_j} \dot{k}_j
$$

with
$$
\dot{k}_j = -\frac{e}{\hbar} E_j \rightarrow \dot{v}_i = \frac{1}{\hbar^2} \sum_j \frac{\partial^2 E}{\partial k_i \partial k_j} (-eE_j)
$$

• effective mass tensor (inverse)

$$
\left(\frac{1}{m^*}\right)_{ij} = \frac{1}{\hbar^2} \sum_j \frac{\partial^2 E(\vec{k})}{\partial k_i \partial k_j}
$$

• eq. of motion

$$
\dot{v}_i = \left(\frac{1}{m^*}\right)_{ij} \left(-eE_j\right)
$$

effective mass approximation m* constant when

$$
E(\vec{k}) = E_0 + \frac{\hbar^2}{2m^*} (k_x^2 + k_y^2 + k_z^2)
$$

Crystal (Bloch) electron in electric field

Force due to electric fieldis equal to time derivative of crystal momentum

$$
\hbar \frac{d\vec{k}}{dt} = -e\vec{E}
$$

Bloch state evolves, after time ∆t:

$$
|\psi_k \to \psi_{k+\Delta k}|
$$

when state reaches BZ k= π/a → -^π/a Bloch oscillations

NB Scattering prevents observation Bloch osc.

Current for Bloch states in a half filled band

Scattering produces steady state

 $|\Delta k|$ = eEτ/ $\hbar \sim 15$ m⁻¹ With τ ~ 10⁻¹⁴ s and E ~1 V/m $<<$ BZ $~10^{10}$ m⁻¹ \rightarrow in reality small change

Currents in bands and holes

• particle current density of d**k** at **k**

$$
d\vec{j}_n = \vec{v}(\vec{k}) \frac{d\vec{k}}{8\pi^3} = \frac{1}{8\pi^3 \hbar} \vec{\nabla}_k E(\vec{k}) d\vec{k}
$$

density states in d**k** 1/(2π)3

• electrical current density integrate over first Brillouin zone

$$
\vec{j} = \frac{-e}{8\pi^3\hbar} \int_{1st \, Br.z.} \vec{\nabla}_k E(\vec{k}) d\vec{k}
$$

different occupied states make different contributions to the current density

• full band

$$
\vec{v}(-\vec{k}) = \frac{1}{\hbar} \vec{\nabla}_{-\vec{k}} E(-\vec{k}) = -\frac{1}{\hbar} \vec{\nabla}_{\vec{k}} E(\vec{k}) = -\vec{v}(\vec{k})
$$

current = 0 \rightarrow insulator

r and reviewith inversion symmetry

$$
E(\vec{k}\uparrow) = E(-\vec{k}\downarrow)
$$

• partially filled band: **E** field redistributes k states symmetry around k=0 lost

• current of positive charge, particles in unoccupied states

$$
\vec{j} = \frac{-e}{8\pi^3} \int_{k\text{ occupied}} \vec{v}(\vec{k}) d\vec{k}
$$

$$
= \frac{-e}{8\pi^3} \int_{1st\text{ Br.}z} \vec{v}(\vec{k}) d\vec{k} - \frac{-e}{8\pi^3} \int_{k\text{ empty}} \vec{v}(\vec{k}) d\vec{k}
$$

$$
= \frac{+e}{8\pi^3} \int_{k\text{ empty}} \vec{v}(\vec{k}) d\vec{k}
$$

(holes)

• holes at the top of the band have positive effective mass!

$$
\dot{\vec{v}} = \frac{1}{\hbar} \frac{d}{dt} \vec{\nabla}_k E(\vec{k}) = -\frac{1}{|m_{\lambda}^*|} \hbar \dot{\vec{k}} = \frac{e}{|m_{\lambda}^*|} \vec{E}
$$

• insulators conduct at T≠0 $n \sim \exp(-E_q / k_B T)$

Scattering of electrons in bands

What did we learn:

- equation of motion \rightarrow electrons/holes accelerate
- Bloch waves in perfect lattice \rightarrow no resistivity $\overline{}$

This cannot be true:

- scattering!
	- deviations from periodicity (defects, lattice vibrations)
	- electron-electron collisions

momentum and energy conservation

$$
E_1 + E_2 = E_3 + E_4 \quad ; \quad \vec{k}_1 + \vec{k}_2 = \vec{k}_3 + \vec{k}_4
$$

2

scattering restricted to narrow k-shell near k_F

$$
\frac{1}{\tau_{e-e}} \sim \rho_{e-e} \sim \left(\frac{k_B T}{E_F}\right)
$$

$$
\left[\n\begin{array}{c}\n\text{near } 300 \text{ K } \tau_{\text{e-e}} \sim 10^{-10} \text{ s} \\
\hline\n\end{array}\n\right]
$$

scattering at a defect or phonon

 $k₁,k₂$ scatters into $k₃,k₄$

Boltzmann equation and relaxation time approximation

Boltzmann eq. describes "non-equilibrium steady state" • driving force due to **E** and **B** field

• dissipation due to scattering

thermal equilibrium distribution E=B=0

$$
f_0(\vec{k}) = f(\vec{r}, \vec{k}, t) \Big|_{\vec{E}=0} = \frac{1}{e^{(E(\vec{k}) - E_F)/k_B T} + 1}
$$

change of *f* in time (t-dt) \rightarrow t + effect of scattering

$$
f(\vec{r}, \vec{k}, t) = f(\vec{r} - \vec{v}dt, \vec{k} + \frac{e\vec{E}}{\hbar}dt, t - dt) + \left(\frac{\partial f}{\partial t}\right)_s dt
$$

expanding up to terms linear in dt \rightarrow Boltzmann equation

$$
\frac{\partial f}{\partial t} + \vec{v} \cdot \vec{\nabla}_r f - \frac{e}{\hbar} \vec{E} \cdot \vec{\nabla}_k f = \left(\frac{\partial f}{\partial t}\right)_s
$$

Relaxation time approximation: rate at which *f* returns to equilibrium ∝ deviation of *f* from *f*⁰

$$
\left(\frac{\partial f}{\partial t}\right)_s = -\frac{f(\vec{k}) - f_0(\vec{k})}{\tau(\vec{k})}
$$

Electrical conductivity of metals

Particle current density

 $j_n = \frac{1}{8\pi^3} \int_{1st \, BZ} \vec{v}(k) f(k) dk$ $\vec{j}_n = \frac{1}{8\pi^3} \int_{1st \, BZ} \vec{v}(\vec{k}) f(\vec{k}) d\vec{k}$ $=\frac{1}{8\pi^3}\int_{1st\,BZ} \vec{v}(k)f(k)$ 81 π

- linear effects in electric field (Ohms law)
- isotropic medium, cubic lattice

8

 π

3

 \hbar

- linearized Boltzmann eq.

σ

$$
\sigma = j_x / E_x = -\frac{e^2}{8\pi^3} \int v_x^2(\vec{k}) \tau(\vec{k}) \frac{\partial f_0}{\partial E} d\vec{k}
$$

 e^2 **c** $v_x^2(k)$ $\int_{E=E_F}$ $\equiv \frac{1}{\sqrt{3}} \Big|_{\sqrt{3}} \Big|_{\sqrt{3}} \frac{1}{\sqrt{3}} \frac{x^{(1)}(k)}{\sqrt{3}} \tau(k)$ only states at Fermi surface important

Fermi surface

Conductivity expressed as integral over the Fermi surface, depends on **v**(E_F) and τ (E_F) $\,$

 $E=E_F$ $\mathcal{U}(\vec{k})$ (\vec{k})

 (k)

 \rightarrow

vk

2

2 \cdot $v^2(k)$ \rightarrow

 (k)

 \rightarrow

 \int_{0}^{x} $\frac{d^{2}y}{dx^{2}}$ $\tau(k)df$

 τ

For parabolic band this reduces to:

$$
\sigma = \frac{e^2 \tau(E_F)}{m^*} n
$$

insert distribution function

Electrical conductivity of metals

Matthiesen's rule

$$
\rho = \rho_0 + \rho_{e-e} + \rho_{ph} + \rho_{mag} + \rho_{CEF} + \dots
$$

$$
\rho_0 = constant
$$

\n
$$
\rho_{e-e} = AT^2
$$

\n
$$
\rho_{ph} = a(T/\theta)^5 \int_0^{\theta/T} \frac{x^5 dx}{(e^x - 1)(1 - e^{-x})}
$$

nesistance of sodium and alloys resistivity of copper-
3 diff. defect concentrations phonon phonon resistance

resistivity of copper-

Electrical conductivity of metals: examples

resistivity of heavy-

resistivity of heavy-
fermion compounds resistivity of superconducting
cuprates: La_{2-x}Sr_xCuO₄ $_{\rm x}$ CuO $_{\rm 4}$

Quantum oscillations and the topology of Fermi surfaces

closed orbits

Motion of electrons and holes in magnetic field Lorentz force \rightarrow

$$
m\frac{d\vec{v}}{dt} = -e(\vec{v} \times \vec{B})
$$

for wave packet m**v**=ħ**k**

$$
\frac{d\vec{k}}{dt} = -\frac{e}{\hbar^2} \left[\vec{\nabla}_k E(\vec{k}) \times \vec{B} \right]
$$

Electrons move: • in plane ⊥ B • tangential to surface of constant E(**k**)

open orbits

Period of orbit in magnetic field

$$
T = \int dt = \frac{\hbar^2}{eB} \oint \frac{d\vec{k}}{[\vec{\nabla}_k E(\vec{k})]_{\perp}}
$$

$$
\oint \frac{dk_{\perp}}{dE} d\vec{k} = \frac{dS}{dE}
$$

Free electrons $S=\pi k^2$ and $E=\hbar^2k^2/2m$

$$
T = \frac{\hbar^2}{eB} \frac{dS}{dE} = \frac{2\pi m^*}{eB}
$$

$$
\omega_c = \frac{2\pi}{T} = \frac{eB}{m^*}
$$

cyclotron frequency

Shubnikov-de Haas effect Resistance in Ga T=1.3 K MAMANA 6 12 10 $H(kG)$

why oscillations?

Landau quantization de Haas-van Alphen effect de Haas van Alphen (1878-1960) (1906-1967) *eBFermi surface area*'s: $S_{n+1} - S_n = \frac{2N}{n+1}$ m^* *T eBEnergy splitting* $E_{n+1} - E_n = \hbar \omega_c = \hbar \omega_c$'s: $S_{n+1} - S_n = \frac{2\pi}{\hbar}$ $\omega_{\rm c} = \hbar \frac{eB}{\rho} = \frac{2\pi}{\rho}$ 2 * : E_{n+1} h $h_{+1}-E_n=\hbar\omega_c=\hbar\frac{\Delta E}{\Delta x}=\frac{2\hbar\omega_c}{T}$ $E_n = (n + \frac{1}{2})\hbar \omega_c$; $\omega_c = \frac{eB}{m^*}$ Landau tubes $S_{F,extr}=(\lambda+n)\Delta S$

e

S

 $\hbar S_{F,}$

 2π

B

 $\Delta\left(\frac{1}{B}\right) =$

: $\Delta \Big|$ $\frac{1}{2}$

Period of oscillations \therefore $\Delta \frac{1}{R}$ = $\frac{HDF,extr}{R}$

Landau tubes cross E_F with period $\Delta(1/B)$ Constant-energy surface $\mathcal{E}(k) = \mathcal{E}_P$

Some numbers:

- period T = 2π/ $\omega_{\rm c}$ = 3.6x10⁻¹¹ s in 1 T
- $\bullet\,$ quantum number: (n+1/2) $\hbar\omega_{\rm c}$ ~ $\sf E_F$ \rightarrow for silver E_F = 5.5 eV \rightarrow n ~ 4.6x10⁴ for B = 1 T
- absence of thermal smearing: $\rm{k_{B}}T/\hbar\omega_{c}$ < 1 $\rm{k_{\rm B}}T/\hbar\omega_c$ = $\rm{k_{\rm B}}m/\hbar e(T/B)$ =1.34(T/B) → low T & high B B

dHvA signal (magnetization) in silver $B || [1,1,1]$ T=1.3 K two periods[→] neck and belly orbits S_{111} (belly)/ S_{111} (neck) = 51

Quantum Hall effect in 2D systems

2D electron gas formed at interface of lattice matched heterostructures or quantum wells

Heterostructures and quantum wells

Heterostructure

Magnetotransport in Hall bar geometry

• Classically

$$
\rho_{xx} = R_{xx} \frac{b}{L} = \frac{V_{xx}}{I} \frac{b}{L}
$$

$$
= \frac{m^*}{ne^2 \tau} = \frac{I}{ne\mu}
$$

mobility $\mu = v_D/E$

$$
\rho_{xy} = R_{xy} = \frac{V_{xy}}{I} = \frac{B}{ne}
$$

- Hall resistance
	- linear in field
	- gives carrier concentration and type (electrons or holes)

The quantum Hall effect

Klaus von Klitzing Nobel Prize Physics 1985 "for the discovery of the quantum Hall effect"

• QHE: ρ_{xy} quantized (resistance standard)

$$
\rho_{xy} = \frac{h}{ie^2} = \frac{25.812}{i} (k\Omega)
$$

• allows precise determination fine structure constant

$$
\alpha = \frac{e^2}{h} \frac{\mu_0 c}{2} \approx \frac{1}{137}
$$

Landau quantization

Energy levels in band *i* split into discrete Landau levels in magnetic field

$$
E_{\mathbf{i},\mathbf{n}} = (n + \frac{1}{2})\hbar\omega_{\mathbf{c}} + g\mu_{\mathbf{B}}B
$$

n = integer Zeeman term

$$
c_{\rm c} = \frac{eB}{m^*} \frac{\text{cyclotron}}{\text{frequency}}
$$

 $\omega_{\rm c}$

Lev Landau1908-1968Nobel Prize Physics 1962 "for his pioneering theories for condensed matter"

Filling factor ^ν

$$
v = \frac{n_{2D}}{N_L} = \frac{n_{2D}h}{eB}
$$

Increasing B $B=0$ (a) (b) (c) E, Energy Density of States *m** $DOS_{2D} = \frac{...}{4}$ $^{2\mathsf{D}}$ $\pi\hbar^2$

Simple "explanation" QHE

- disorder/impurities → extended and localisedstates in Landau levels
- with increasing field B Landau levels pushed to above $\mathsf{E}_\mathsf{F} \to$ plateau-plateau transitions
- conduction when Landau level in extended states
- width extended states $\rightarrow 0$ when $\mathsf{T} \to 0$

Typical numbers

• Energy distance between levels – *k*B*T*~ 25 meV near 300 K – hωc ~ 1.6 meV/T (*m**= 0.067*m*e) $k_{\text{\tiny B}}$ *T* << \hbar $\omega_{\text{\tiny c}}$ \rightarrow T< 4 K $\omega_{\rm c} = eB/m^*$

\bullet Filling fraction

– typical *n_{2D}=* 2x10¹⁵ m⁻² – quantum limit ^ν =1 [→] *B*~ 8.25 T

$$
v = \frac{n_{2D}}{N_L} = \frac{n_{2D}h}{eB}
$$

high B/T needed

InGaAs/GaAs quantum well $n = 2x10^{15} m^{-2}$ $T = 0.08 - 4.2$ K

Fractional quantum Hall effect

$$
\rho_{xy} = \frac{h}{ve^2} = \frac{25.812}{v} (k\Omega)
$$

ν = 1/3, 2/3, 1/5, 2/5 etc.

fractional quantum Hall effect in high mobility GaAs/AlGaAs heterostructure T= 0.15 K